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(71) Applicant:

HYNIX SEMICONDUCTOR INC.

(72) Inventor:

KIM, SU HO

KWON, O JEONG

LEE, CHANG JIN

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(54) Title of Invention

METHOD OF FORMING TEST PATTERN FOR MEASURING ISOLATION LAYER

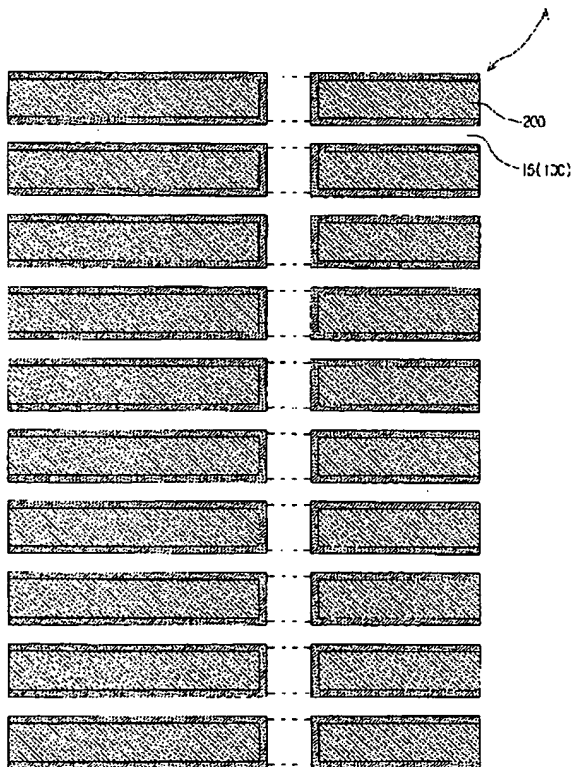
Representative drawing

(57) Abstract:

PURPOSE: A method of forming a test pattern for measuring an isolation layer is provided to improve the productivity of a semiconductor device by measuring accurately a height of an isolation layer.

CONSTITUTION: An isolation layer(15) for defining an active region(100) of a semiconductor device is formed on a semiconductor substrate. A test pattern for measuring the isolation layer is formed thereon. The semiconductor substrate of an isolation region(100) is etched by performing a photo etching process using an isolation mask. A trench is formed by the etching process. The trench is buried as an insulating material. An isolation layer(100) is formed by performing a planarization process.

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